

11th "Trento" Workshop on Advanced Silicon Radiation Detectors

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LPNHE

Book of Abstracts

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3D Sensors for the HL-LHC

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Beam test results of highly irradiated planar and 3D pixel sensors for the Phase II Upgrade of the CMS pixel detector

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Beam test results of irradiated 3D pixel sensors for the CMS-TOTEM Precision Proton Spectrometer

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Characterisation of thin irradiated epitaxial silicon sensors for the CMS phase II pixel upgrade

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Charge Collection Properties of depleted Monolithic Active Pixel Sensors

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Comprehensive radiation damage test and modelling of p-type silicon detectors for high-luminosity operations

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Detector development at the Paul-Scherrer-Institut (PSI)

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Development of passive pixel sensors using a commercial 150nm CMOS technology on high resistivity silicon

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Electric field, mobility and trapping in Si detectors irradiated with neutrons and protons up to $1e17 \text{ n}_{\text{eq}}/\text{cm}^2$

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First Inverted Low Gain Avalanche Detector fabrication at IMB-CNM

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Initial results from a new generation of 3D Sensors for HL-LHC

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Initial results from the electrical characterisation of planar p-on-n sensors with active/slim-edge for the next generation of FELs

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Investigation on the radiation resistance of HV-CMOS and pin diodes using a Transient Current Technique based on the Two-Photon-Absorption Process

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Transient Current Techniques (TCT) based on laser-induced photo-currents produced by Single Photon Absorption (SPA) processes have been extensively used during the last two decades as a powerful tool to study many of the properties relevant to operation of semiconductor detectors.

Very recently, an innovative Transient Current Technique was introduced where the free charge carriers are created in a Two-Photon-Absorption (TPA) process induced by a focused femto-second laser pulse with a wavelength of 1300nm. The fact that in a TPA process the absorption of the light depends on the square of the intensity of the light beam used for the current generation allows a localized TPA-induced electron-hole pair creation in a micrometric scale voxel centered on the laser waist. As a consequence, this new technique opens the possibility to carry out a 3D mapping of the sensor's space-charge properties with micrometric resolution.

Due to its intrinsic spatial resolution, the TPA-TCT technique should be a very appropriate choice for the characterization of the alterations of the sensor's active (charge collecting) volume induced by radiation damage and especially for the case of partially depleted sensors as it is the case of the carrier collecting n-well implemented in HV-CMOS sensors.

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Latest development in HPK/KEK n⁺-in-p planar pixel sensors for very high radiation environments

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Low Gain Avalanche Detectors TCAD Radiation Damage Analysis

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Where we present our last results on radiation damage analysis of Low Gain Avalanche Detectors using the Synopsys TCAD suite and different well established radiation damage models. Our main conclusions point to this device could work reasonably well up to $\sim 1e14$ n_eq/cm².

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Low Gain Avalanche Diode gallium process flow simulation studies

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Monolithic CMOS ASIC Developments

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Performance of Edgeless Silicon Pixel Sensors on p-type substrate for the ATLAS High-Luminosity Upgrade

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Progress in Ultra-Fast Silicon Detectors

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Recent results with hybrid pixel assemblies for the CLIC vertex detector

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Results on thin n in p Planar Pixels from INFN R&D

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Reverse bias current characterisation of silicon strip sensors and shallow radiation damage generation

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SPS Test Beam characterisation results with CCPDv4 capacitively coupled to FEI4

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Silicon pixel tracking detector with ultra-precise time resolution

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Status of 3D detector activities at CNM

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Status of LGAD CNM fabrications

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Study of New ADVACAM Active Edge Sensor Technology for AT-LAS Upgrade

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TCAD simulations of High-Voltage-CMOS pixel structures for the CLIC vertex detector

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TCAD simulations of LGAD devices using Silvaco software

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TCT measurements of HV-CMOS test structures irradiated with neutrons

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The first reticle size HV-CMOS sensor demonstrator for ATLAS pixel layers

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The impact and persistence of static surface charges on differently passivated silicon strip sensors

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The upgraded ATLAS Pixel detector and its performance during run-2 in 2015

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Tracking in 4 dimensions

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Validation strategy for the simulation of highly irradiated silicon pixel sensors

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